MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICES

Abstract

A wiring circuit layer 2 having a connecting conductor part 21 that can be connected to an electrode 31 of a semiconductor element 3 is formed on a metal support substrate 1 in a way such that the wiring circuit layer can be separated from the substrate 1, and that the connecting conductor part 21 is exposed on the upper face of the wiring circuit layer. The wiring circuit layer 2 is laminated on the element 3 while in a wafer state, and the connecting conductor part 21 and the electrode 31 are connected. Subsequently, the support substrate 1 is peeled from the wiring circuit layer 2, and the wafer is diced, whereby individual semiconductor devices are obtained.

Figure 1